Abstracts

Conversion Losses in GaAs Schottky-Barrier Diodes (Short Papers)

O. Von Roos and K.-L. Wang. "Conversion Losses in GaAs Schottky-Barrier Diodes (Short Papers)." 1986 Transactions on Microwave Theory and Techniques 34.1 (Jan. 1986 [T-MTT]): 183-188.

The conversion losses of a Schottky-barrier diode have been calculated for a set of realistic diode parameters. It is found that previous work overestimated the substrate losses by 30 percent. It is also shown that a lightly doped epitaxial layer will decrease the barrier capacitance and with properly designed thickness will avoid any resistance losses due to this layer. Parasitic losses can thus be reduced substantially.

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